Evelina Domashevskaya

List of Publications by Year
in descending order

186	1,670	331670	434195
papers	citations	21 h-index	31 g-index

188	188	188	1375
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Application of semiconductor gas sensors for medical diagnostics. Sensors and Actuators B: Chemical, 1999, 59, 26-29.	7.8	120
2	Synthesis of nanocrystalline hydroxyapatite by precipitation using hen's eggshell. Ceramics International, 2013, 39, 4539-4549.	4.8	108
3	A study by XPS and XRS of the participation in chemical bonding of the 3d electrons of copper, zinc and gallium. Journal of Electron Spectroscopy and Related Phenomena, 1975, 6, 231-238.	1.7	60
4	XPS and XES emission investigations of dâ€“p resonance in some copper chalcogenides. Journal of Electron Spectroscopy and Related Phenomena, 2001, 114-116, 901-908.	1.7	37
5	dâ€”s, p Resonance and Electronic Structure of Compounds, Alloys, and Solid Solutions. Physica Status Solidi (B): Basic Research, 1981, 105, 121-127.	1.5	36
6	XANES and XPS investigations of surface defects in wire-like SnO2 crystals. Physics of the Solid State, 2015, 57, 153-161.	0.6	36
7	Determination of the phase composition of surface layers of porous silicon by ultrasoft X-ray spectroscopy and X-ray photoelectron spectroscopy techniques. Journal of Electron Spectroscopy and Related Phenomena, 2001, 114-116, 895-900.	1.7	32
8	Optical characteristics of porous silicon structures. Technical Physics, 2014, 59, 224-229.	0.7	27
9	Raman investigation of low temperature AlGaAs/GaAs(100) heterostructures. Physica B: Condensed Matter, 2010, 405, 2694-2696.	2.7	26
10	Valence-level structure of phosphides of 3d-metals on the basis of XRS and ESCA data. Journal of Electron Spectroscopy and Related Phenomena, 1979, 16, 441-453.	1.7	25
11	Structural and optical investigations of AlxGa1â^'xAs:Si/GaAs(100) MOCVD heterostructures. Physica B: Condensed Matter, 2010, 405, 4607-4614.	2.7	25
12	Participation of d-electrons of metals of groups I, II, and III in chemical bonding with sulphur. Journal of Electron Spectroscopy and Related Phenomena, 1976, 9, 261-267.	1.7	24
13	XRD, AFM and IR investigations of ordered AlGaAs2 phase in epitaxial AlxGa1â€“xAs/GaAs (100) heterostructures. Surface and Interface Analysis, 2006, 38, 828-832.	1.8	24
14	On a study of the valence band structure of boron and some of its compounds by the X-ray spectral method. Journal of the Less Common Metals, 1976, 47, 189-193.	0.8	23
15	SnOx obtaining by thermal oxidation of nanoscale tin films in the air and its characterization. Thin Solid Films, 2007, 515, 6350-6355.	1.8	23
16	XPS and XANES studies of SnO x nanolayers. Journal of Structural Chemistry, 2008, 49, 80-91.	1.0	23
17	Evolution of nanoporous silicon phase composition and electron energy structure under natural ageing. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1651-1655.	0.8	23
18	The substructure and luminescence of low-temperature AlGaAs/GaAs(100) heterostructures. Semiconductors, 2010, 44, 184-188.	0.5	23

#	Article	IF	Citations
19	Effect of silicon on relaxation of the crystal lattice in MOCVDâ€“hydride Al x Ga1 â^' x As:Si/GaAs(100) heterostructures. Semiconductors, 2011, 45, 481-492.	0.5	23
20	Spinodal Decomposition of Ga x In1â^'x As y P1â^'y Quaternary Alloys. Semiconductors, 2011, 45, 1433-1440.	0.5	23
21	Study of the morphological growth features and optical characteristics of multilayer porous silicon samples grown on n-type substrates with an epitaxially deposited p +-layer. Semiconductors, 2012, 46, 1079-1084.	0.5	23
22	Structural features and surface morphology of AlxGayIn1â^'xâ^'yAszP1â^'z/GaAs(100) heterostructures. Applied Surface Science, 2013, 267, 181-184.	6.1	23
23	Role of Noble Metal dâ€States in the Formation of the Electron Structure of Ternary Sulphides. Physica Status Solidi (B): Basic Research, 1981, 106, 429-435.	1.5	20
24	Effect of natural aging on photoluminescence of porous silicon. Technical Physics Letters, 2011, 37, 789-792.	0.7	20
25	X-ray diffraction and IR spectroscopy investigation of synthesized and biogenic nanocrystalline hydroxyapatite. Journal of Surface Investigation, 2011, 5, 1162-1167.	0.5	19
26	Problems of the OPW Method. II. Calculation of the Band Structure of ZnS and CdS. Physica Status Solidi (B): Basic Research, 1980, 97, 631-640.	1.5	18
27	Spin compensation temperatures in the mean-field approximation of a mixed spin-2 and spin-5/2 Ising ferrimagnetic system. Physica A: Statistical Mechanics and Its Applications, 2009, 388, 4713-4718.	2.6	18
28	Structural and spectral features of MOCVD Al x Ga y In1 â^' x â^' y As z P1 â^' z /GaAs (100) alloys. Semiconductors, 2012, 46, 719-729.	0.5	18
29	TEM and XANES investigations and optical properties of SnO nanolayers. Surface and Interface Analysis, 2006, 38, 514-517.	1.8	17
30	Silicon nanocrystals in SiO2 matrix obtained by ion implantation under cyclic dose accumulation. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 38, 16-20.	2.7	17
31	A novel approach to the electronic structure and surface composition investigations of tin-oxygen system materials by means of X-ray absorption spectroscopy combined with ab initio calculations. Computational Materials Science, 2016, 121, 119-123.	3.0	17
32	Integration over the Twoâ€Dimensional Brillouin Zone. Physica Status Solidi (B): Basic Research, 1985, 129, 293-299.	1.5	16
33	Electronic structure of undoped and doped SnOx nanolayers. Thin Solid Films, 2013, 537, 137-144.	1.8	16
34	Theoretical and experimental study of the electronic structure of tin dioxide. Physics of the Solid State, 2014, 56, 1748-1753.	0.6	16
35	Investigations of the electron energy structure and phase composition of porous silicon with different porosity. Journal of Electron Spectroscopy and Related Phenomena, 2007, 156-158, 445-451.	1.7	15
36	Effect of the temperatures on structural and optical properties of tin oxide (SnOx) powder. Physica B: Condensed Matter, 2010, 405, 313-317.	2.7	15

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37	Spectral features of Coâ€“Geâ€“Te amorphous thin film. Optics and Laser Technology, 2011, 43, 20-24.	4.6	15
38	Influence of natural aging on photoluminescence from porous silicon. Technical Physics, 2012, 57, 305-307.	0.7	15
39	Investigations of the composition of macro-, micro- and nanoporous silicon surface by ultrasoft X-ray spectroscopy and X-ray photoelectron spectroscopy. Applied Surface Science, 2015, 359, 550-559.	6.1	15
40	XANES, USXES and XPS investigations of electron energy and atomic structure peculiarities of the silicon suboxide thin film surface layers containing Si nanocrystals. Surface and Interface Analysis, 2010, 42, 891-896.	1.8	14
41	Optical properties of porous silicon processed in tetraethyl orthosilicate. Technical Physics, 2013, 58, 284-288.	0.7	14
42	Electron structure of porous silicon obtained without the use of HF acid. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1557-1560.	0.8	13
43	APW-LCAO energy bands and fundamental absorption in silver chloride crystal. Solid State Communications, 1981, 40, 559-562.	1.9	12
44	Synchrotron investigations of the initial stage of tin nanolayers oxidation. Journal of Electron Spectroscopy and Related Phenomena, 2007, 156-158, 340-343.	1.7	12
45	Compensation temperatures induced by longitudinal fields in a mixed spin Ising ferrimagnet. Solid State Communications, 2010, 150, 1253-1257.	1.9	12
46	Structure and composition of metal-substituted calcium-deficient hydroxyapatite. Journal of Surface Investigation, 2014, 8, 1128-1136.	0.5	12
47	Phase composition of the buried silicon interlayers in the amorphous multilayer nanostructures [(<scp>Co</scp>₄₅<scp>Fe</scp>₄₅<scp>Zr</scp>₁₀)/aâ€<scp>Si</scp>:<scp>H</scp> and [(<scp>Co</scp>₄₅<scp>Fe</scp>₄₅<scp>Zr</scp>₁₀)₃₅(<scp>Al</scp><sub> Surface and Interface Analysis, 2018, 50, 1265-1270.	1.8	12
48	Electronic structure of rhenium disilicides. Journal of Physics Condensed Matter, 2002, 14, 6833-6839.	1.8	11
49	USXES AND OPTICAL PHENOMENA IN Si LOW-DIMENSIONAL STRUCTURES DEPENDENT ON MORPHOLOGY AND SILICON OXIDE COMPOSITION ON Si SURFACE. Surface Review and Letters, 2002, 09, 1047-1052.	1.1	11
50	Preparation of porous silicon nanocomposites with iron and cobalt and investigation of their electron structure by X-ray spectroscopy techniques. Technical Physics Letters, 2009, 35, 827-830.	0.7	11
51	A soft X-ray synchrotron study of the charge state of iron ions in the ferrihydrite core of the ferritin Dps protein in Escherichia coli. Biophysics (Russian Federation), 2016, 61, 705-710.	0.7	11
52	A study of the local electronic and atomic structure in a-SixC1â^'x amorphous alloys using ultrasoft X-ray emission spectroscopy. Semiconductors, 2005, 39, 830-834.	0.5	10
53	Structure and photoluminescence properties of SnO₂nanowires synthesized from SnO powder. EPJ Applied Physics, 2009, 48, 10603.	0.7	10
54	Photoluminescence properties of heavily doped heterostructures based on (Al x Ga1 â^' x As)1 â^' y Si y solid solutions. Physics of the Solid State, 2013, 55, 2169-2172.	0.6	10

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55	Localâ€Densityâ€Functional Approximation to the Energy Band Structure of TmS Using the Selfâ€Consistent Relativistic Linearizedâ€Augmentedâ€Plancâ€Wave Method. Physica Status Solidi (B): Basic Research, 1984, 121, 241-253.	1.5	9
56	Synchrotron investigations of the specific features in the electron energy spectrum of silicon nanostructures. Physics of the Solid State, 2004, 46, 345-350.	0.6	9
57	XANES and USXES investigations of interatomic interaction at the grain boundaries in nanocomposites (Co41Fe39B20)x(SiO2)1â^'x. Journal of Electron Spectroscopy and Related Phenomena, 2007, 156-158, 180-185.	1.7	9
58	Composition and parameters of domains resulting from spinodal decomposition of quaternary alloys in epitaxial GaInP/Ga x In1 â^' x As y P1 â^' y /GaInP/GaAs(001) heterostructures. Semiconductors, 2008, 42, 1069-1075.	0.5	9
59	Structural and optical properties of low-temperature hydride-MOCVD AlGaAs/GaAs(100) heterostructures based on omission solid solutions. Semiconductors, 2009, 43, 1610-1616.	0.5	9
60	AES and XPS investigations of the surface layers of porous silicon with Fe, Co, and Ni embedded pores. Journal of Surface Investigation, 2012, 6, 106-110.	0.5	9
61	XANES investigations of interatomic interactions in multilayered nanostructures (Co45Fe45Zr10/a-Si)40 and (Co45Fe45Zr10/SiO2)32. Physics of the Solid State, 2013, 55, 1294-1303.	0.6	9
62	X-Ray photoelectron spectroscopy investigations of atomic interactions in surface layers of multilayered nanostructures (Co45Fe45Zr10/a-Si)40 and (Co45Fe45Zr10/SiO2)32. Physics of the Solid State, 2014, 56, 2294-2306.	0.6	9
63	The Influence of Relative Content of a Metal Component in a Dielectric Matrix on the Formation and Dimensions of Cobalt Nanocrystallites in Cox(MgF2)100Ââ€“Âx Film Composites. Physics of the Solid State, 2019, 61, 71-79.	0.6	9
64	Problems of the OPW method. I. Transition metals. Physica Status Solidi (B): Basic Research, 1979, 94, 51-62.	1.5	8
65	Density of states and photoconductivity in hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1987, 90, 135-138.	3.1	8
66	Temperature dependence of residual stress in epitaxial GaAs/Si(100) films determined from photoreflectance spectroscopy data. Semiconductors, 2000, 34, 73-80.	0.5	8
67	Structure, elemental composition, and mechanical properties of films prepared by radio-frequency magnetron sputtering of hydroxyapatite. Glass Physics and Chemistry, 2008, 34, 608-616.	0.7	8
68	XPS study of the oxidation of nanosize Ni/Si(100) films. Journal of Structural Chemistry, 2011, 52, 115-122.	1.0	8
69	Band structure and density of states in SiP₂. Physica Status Solidi (B): Basic Research, 1975, 72, 661-665.	1.5	7
70	Influence of water vapor adsorption on the C-V characteristics of heterostructures containing porous silicon. Technical Physics, 2003, 48, 1442-1448.	0.7	7
71	Vegardâ€™s law and superstructural phases in AlxGa1â^'x As/GaAs(100) epitaxial heterostructures. Semiconductors, 2005, 39, 336-342.	0.5	7
72	Investigations of porous InP properties by XRD, IR, USXES, XANES and PL techniques. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 147, 144-147.	3.5	7

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73	XANES and USXES studies of interatomic interactions in (Co41Fe39B20) x (SiO2)1 â^' x nanocomposites. Physics of the Solid State, 2008, 50, 139-145.	0.6	7
74	Relaxation of crystal lattice parameters and structural ordering in In x Ga1 â^' x As epitaxial alloys. Semiconductors, 2010, 44, 1106-1112.	0.5	7
75	Synchrotron investigations of electronic and atomic-structure peculiarities for silicon-oxide filmsâ€™ surface layers containing silicon nanocrystals. Journal of Surface Investigation, 2011, 5, 958-967.	0.5	7
76	Properties of epitaxial (Al x Ga1 â^' x As)1 â^' y C y alloys grown by MOCVD autoepitaxy. Semiconductors, 2013, 47, 7-12.	0.5	7
77	Excitation of luminescence of the nanoporous bioactive nanocrystalline carbonate-substituted hydroxyapatite for early tooth disease detection. Results in Physics, 2017, 7, 3853-3858.	4.1	7
78	Electronic structure of a-Si3N4 : AB initio cluster calculations and soft X-ray emission spectroscopy study. Journal of Non-Crystalline Solids, 1989, 114, 495-497.	3.1	6
79	X-ray spectroscopic study of electronic structure of amorphous silicon and silicyne. Semiconductors, 2001, 35, 956-961.	0.5	6
80	Infrared reflection spectra of multilayer epitaxial heterostructures with embedded InAs and GaAs layers. Semiconductors, 2008, 42, 1055.	0.5	6
81	Composition and reactivity of porous silicon nanopowders. Inorganic Materials, 2012, 48, 965-970.	0.8	6
82	Synchrotron study of the formation of nanoclusters in Al2O3/SiO x /Al2O3/SiO x /â€¦/Si(100) multilayer nanostructures. Semiconductors, 2013, 47, 1316-1323.	0.5	6
83	Synchrotron studies of SnO2 wire-like crystals. Journal of Surface Investigation, 2014, 8, 111-116.	0.5	6
84	Interatomic interactions at interfaces of multilayered nanostructures (Co45Fe45Zr10/a-Si)40 and (Co45Fe45Zr10/SiO2)32. Physics of the Solid State, 2016, 58, 1024-1033.	0.6	6
85	XANES study of interatomic interactions in (CoFeZr) x (SiO2)1â€“x nanocomposites. Bulletin of the Russian Academy of Sciences: Physics, 2008, 72, 448-452.	0.6	5
86	Phase formation under the effect of spinodal decomposition in epitaxial alloys of Ga x In1 â^' x P/GaAs(100) heterostructures. Semiconductors, 2009, 43, 1221-1225.	0.5	5
87	Interference phenomena of synchrotron radiation in TEY spectra for silicon-on-insulator structure. Journal of Synchrotron Radiation, 2012, 19, 609-618.	2.4	5
88	Synthesis of europium-doped zinc oxide micro- and nanowires. Russian Journal of Physical Chemistry A, 2014, 88, 108-111.	0.6	5
89	Specific features of the sol-gel formation and optical properties of 3d metal/porous silicon composites. Semiconductors, 2014, 48, 551-555.	0.5	5
90	Peculiarities of the electronic structure and phase composition of amorphous (SiO2) x (a-Si: H) xâ€“1 composite films according to X-ray spectroscopy data. Technical Physics Letters, 2015, 41, 1010-1012.	0.7	5

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91	Atomic and electronic structure peculiarities of silicon wires formed on substrates with varied resistivity according to ultrasoft X-ray emission spectroscopy. Technical Physics Letters, 2015, 41, 344-347.	0.7	5
92	Formation of silicon nanocrystals in multilayer nanoperiodic a-SiO x /insulator structures from the results of synchrotron investigations. Semiconductors, 2017, 51, 349-352.	0.5	5
93	Electronic structure and phase composition of dielectric interlayers in multilayer amorphous nanostructure [(CoFeB)60C40/SiO2]200. Physics of the Solid State, 2017, 59, 168-173.	0.6	5
94	Photoluminescence Properties of Nanoporous Nanocrystalline Carbonate-Substituted Hydroxyapatite. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2018, 124, 187-192.	0.6	5
95	Density of States and Photoconductivity of Hydrogenated Amorphous Silicon. Physica Status Solidi (B): Basic Research, 1986, 138, 647-653.	1.5	4
96	Theoretical Xâ€•ray Emission Study of Highâ€•T_c Superconductor YBa₂Cu₃O₇ Thin Films. Physica Status Solidi (B): Basic Research, 1994, 185, 179-187.	1.5	4
97	Generalized multilayer model for the quantitative analysis of the electromodulation components of the electroreflectance and photoreflectance spectra of semiconductors in the region of the E 0 fundamental transition. Semiconductors, 2000, 34, 1045-1051.	0.5	4
98	Infrared reflectance spectra and morphologic features of the surface of epitaxial AlxGa1â^'x As/GaAs(100) heterostructures with the ordered AlGaAs2 phase. Semiconductors, 2006, 40, 406-413.	0.5	4
99	Kinetics of resistive response of SnO2 â^' x thin films in gas environment. Semiconductors, 2008, 42, 481-485.	0.5	4
100	Investigation of porous InP by X-ray diffraction, IR spectroscopy, USXES, XANES spectroscopy, and photoluminescence. Bulletin of the Russian Academy of Sciences: Physics, 2008, 72, 439-442.	0.6	4
101	The formation of tin oxides in thin-film Sn/C/KCl(100) structures. Crystallography Reports, 2009, 54, 110-115.	0.6	4
102	Temperature dependence of liquid volume. Technical Physics, 2009, 54, 1082-1084.	0.7	4
103	Synchrotron radiation interference in front of the silicon absorption edge for silicon-on-insulator structures. Journal of Surface Investigation, 2011, 5, 141-149.	0.5	4
104	Synchrotron investigation of the multilayer nanoperiodical Al₂O₃/SiO/Al₂O₃/SiOâ€¦Si structure formation. Surface and Interface Analysis, 2012, 44, 1182-1186.	1.8	4
105	Synchrotron investigations of Si/Mo/Siâ€¦c-Si (100) multilayer nanoperiodic structures. Physics of the Solid State, 2013, 55, 634-641.	0.6	4
106	Atomic and electronic structure of amorphous and nanocrystalline layers of semi-insulating silicon produced by chemical-vapor deposition at low pressures. Journal of Surface Investigation, 2015, 9, 1228-1236.	0.5	4
107	Formation of Si nanocrystals in multilayered nanoperiodic Al2O3/SiO x /Al2O3/SiO x /.../Si(100) structures: Synchrotron and photoluminescence data. Semiconductors, 2015, 49, 409-413.	0.5	4
108	X-ray and x-ray electron spectroscopy of new materials. Journal of Structural Chemistry, 2017, 58, 1057-1060.	1.0	4

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109	Synchrotron investigations of the electron structure of silicon nanocrystals in a SiO2 matrix. Journal of Surface Investigation, 2007, 1, 55-59.	0.5	3
110	Electronic and energy structure and X-ray spectra of Zn3P2 and Cd3P2 and their solid solution (Cd0.5Zn0.5)3P2. Journal of Structural Chemistry, 2008, 49, 59-62.	1.0	3
111	X-ray photoelectron spectroscopy of tin oxide nanolayers. Bulletin of the Russian Academy of Sciences: Physics, 2008, 72, 504-509.	0.6	3
112	Electron structure of iron and cobalt nanocomposites on the basis of porous silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1656-1660.	0.8	3
113	Peculiarities of electron-energy structure of surface layers of porous silicon formed on p-type substrates. Inorganic Materials, 2012, 48, 1291-1297.	0.8	3
114	The synthesis and optical properties of different zinc oxide nanostructures. Russian Journal of Physical Chemistry A, 2013, 87, 2246-2252.	0.6	3
115	Composition and optical properties of amorphous a-SiO x :H films with silicon nanoclusters. Semiconductors, 2016, 50, 212-216.	0.5	3
116	Electronic structure and phase composition of silicon oxide in the metal-containing composite layers of a [(Co40Fe40B20)34(SiO2)66/C]46 multilayer amorphous nanostructure with carbon interlayers. Inorganic Materials, 2017, 53, 930-936.	0.8	3
117	IR Spectroscopic Study of Interatomic Interaction in [(CoFeB)60C40/SiO2]200 and [(CoFeB)34(SiO2)66/C]46 Multilayer Nanostructures with Metal-Containing Composite Layers. Inorganic Materials, 2018, 54, 140-146.	0.8	3
118	A study of multilayer nanostructures [(Co₄₅Fe₄₅Zr₁₀)₃₅(Al₂O₃)₆₅/a-Si:H and [(Co₄₅Fe₄₅Zr₁₀)₃₅(Al₂O₃)₆₅/a-Si] by means of XRD, XRR, IR spectroscopy, and USXES. EPJ Applied Physics, 2019, 87, 21301.	0.7	3
119	Effect of Phase Transformations of a Metal Component on the Magneto-Optical Properties of Thin-Films Nanocomposites (CoFeZr)x (MgF2)100â^'x. Nanomaterials, 2021, 11, 1666.	4.1	3
120	XRD and Raman Study of Low Temperature AlGaAs/GaAs (100) Heterostructures. NATO Science for Peace and Security Series B: Physics and Biophysics, 2010, , 225-236.	0.3	3
121	Electronic structure of the full-Heusler Co$$_{2-x}$$Fe$$_{1+x}$$Si and half-Heusler CoFeSi alloys obtained by first-principles calculations and ultrasoft X-ray emission spectroscopy. European Physical Journal B, 2022, 95, 1.	1.5	3
122	The electron structure and interatomic interactions in the bpxas1â^'x system. Journal of the Less Common Metals, 1979, 67, 229-235.	0.8	2
123	Changing of density of states in amorphous silicon nitride at degradation of its electric propertoes using soft X-ray spectroscopy. Journal of Non-Crystalline Solids, 1987, 97-98, 827-830.	3.1	2
124	Silicide formation in thin film Ptâ€“Si(111) structure by USXES data. Thin Solid Films, 1997, 298, 135-137.	1.8	2
125	A combined technique for studying the multicomponent spectra of photoreflection from semiconductors. Semiconductors, 2002, 36, 48-53.	0.5	2
126	Influence of laser pump density on the characteristic time constant and the intermediate-field electromodulation E 0 component of the photoreflectance signal. Semiconductors, 2002, 36, 153-156.	0.5	2

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127	E 0 photoreflectance spectra of GaAs: Identification of the features related to impurity transitions. Semiconductors, 2002, 36, 259-262.	0.5	2
128	Synchrotron investigations of an electron energy spectrum in IIIâ€“V-based nanostructures. Semiconductors, 2003, 37, 992-997.	0.5	2
129	Optical properties of SnO2â^'x nanolayers. Technical Physics Letters, 2006, 32, 782-784.	0.7	2
130	Features of atomic and electronic structure of oxides on porous silicon surface according to XANES data. Journal of Surface Investigation, 2010, 4, 384-389.	0.5	2
131	Investigations of Porous Silicon with Deposited 3D-Metals by Auger- and Ultrasoft X-Ray Emission Spectroscopy. Journal of Nanoscience and Nanotechnology, 2012, 12, 8806-8810.	0.9	2
132	Variations of the optical characteristics of nano-, meso-, and macroporous silicon with time. Technical Physics, 2015, 60, 1096-1100.	0.7	2
133	Composition of nanocomposites based on thin layers of tin on porous silicon formed by magnetron sputtering. Physica B: Condensed Matter, 2017, 504, 1-8.	2.7	2
134	On the Morphology and Optical Properties of Molybdenum Disulfide Nanostructures from a Monomolecular Layer to a Fractal-Like Substructure. Semiconductors, 2019, 53, 923-929.	0.5	2
135	Oscillating fine structure of x-ray absorption and atomic structure of metallic layers in a magnetic multilayer nanostructure (Đ¡o45Fe45Zr10/SiO2)n. Materials Research Express, 2019, 6, 1150g9.	1.6	2
136	Influence of the Crystal Structure of the Nucleus on the Morphology of t-ZnO Tetrapods. Crystallography Reports, 2019, 64, 212-215.	0.6	2
137	Effect of Process Conditions on the Structure and Optical Properties of MoO3 Produced by Vapor Transport Deposition. Inorganic Materials, 2019, 55, 49-58.	0.8	2
138	X-ray spectral and X-ray electron study of complex oxides of Rh. Journal of Structural Chemistry, 1979, 20, 37-41.	1.0	1
139	Local non-stoichiometry in superconducting and ferroelectric films of complex oxides. Ferroelectrics, 1992, 130, 175-185.	0.6	1
140	AES and USXES investigations of the phase transformation in the surface layers of V-Si/SiO2/Si thin films structure stimulated by oxygen annealing. Journal of Electron Spectroscopy and Related Phenomena, 1995, 76, 511-516.	1.7	1
141	Title is missing!. Russian Physics Journal, 2002, 45, 405-413.	0.4	1
142	Role of the buffer porous layer and dysprosium doping in GaInPâ€porGaAsâ€GaAs heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1694-1696.	0.8	1
143	Atomic and electronic structure of the surface of porous silicon layers. Russian Journal of General Chemistry, 2010, 80, 1128-1135.	0.8	1
144	Structural, microstructural and optical properties of multiphase Geâ€“Coâ€“Te system. Physica B: Condensed Matter, 2010, 405, 2107-2109.	2.7	1

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145	Structural and optical properties of porous silicon prepared from a p +-epitaxial layer on n-Si(111). Technical Physics, 2013, 58, 404-407.	0.7	1
146	The problem of XANES spectrum interpretation measured by TEY technique at different photon glancing angles. Journal of Electron Spectroscopy and Related Phenomena, 2013, 191, 35-40.	1.7	1
147	Specific features of the electronic and atomic structures of silicon single crystals in the aluminum matrix. Physics of the Solid State, 2014, 56, 2543-2547.	0.6	1
148	Ab initio calculation and synchrotron X-ray spectroscopy investigations of tin oxides near the Sn L 3 absorption edges. Physics of the Solid State, 2016, 58, 2379-2384.	0.6	1
149	Small-angle diffraction by heterogeneous composite nanostructures based on (Co45Fe45Zr10)35(Al2O3)65. Bulletin of the Russian Academy of Sciences: Physics, 2016, 80, 1407-1410.	0.6	1
150	The electronic structure peculiarities of a strained silicon layer in silicon-on-insulator: Experimental and theoretical data. Applied Surface Science, 2016, 382, 331-335.	6.1	1
151	Specific features of the atomic structure of metallic layers of multilayered (CoFeZr/SiO2)32 and (CoFeZr/a-Si)40 nanostructures with different interlayers. Physics of the Solid State, 2017, 59, 385-391.	0.6	1
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183	Ð’Ð»Ð¸ÐÐ½Ð¸Ðµ Ñ€ÐµÐ¶Ð¸Ð¼Ð¾Ð² ÑÐ»ÐµÐºÑ‚Ñ€Ð¾Ð½Ð½Ð¾-Ð¸Ð¾Ð½Ð½Ð¾Ð³Ð¾ Ñ‚Ñ€Ð°Ð²Ð»ÐµÐ½Ð¸Ñ Ð½Ð°	0.2	0
184	Ð¢Ð¾Ð¿Ð¾Ð»Ð¾Ð³Ð¸Ñ‡ÐµÑÐºÐ°Ñ•Ð¼Ð¾Ð´ÐµÐ»Ð¬ ÑÑ€ÑƒÐºÑ‚ÑƒÑ€ Ð¸Ð½ÐµÐ»Ð¸Ð½ÐµÐ¹Ð½Ð°Ñ•Ð¼Ð¾Ð´Ðµ	0.3	0
185	Investigation of the Magnetic Properties of Amorphous Multilayer Nanostructures [(CoFeB)60C40/SiO2]200 and [(CoFeB)34(SiO2)66/C]46 by the Transversal Kerr Effect. Kondensirovannye Sredy Mezhfaznye Granitsy, 2020, 22, 438-445.	0.3	0
186	Ð’Ð»Ð¸ÐÐ½Ð¸Ðµ ÑÐ»ÐµÐ±Ð¾Ð³Ð¾ Ð¿Ð¾Ñ€ÑŒÐ½Ð¾Ð³Ð¾ ÑÐ»ÐµÐºÑ‚Ñ€Ð¾Ð½Ð½Ð¾-Ð¸Ð¾Ð½Ð	0.3	0